

SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

P-Channel Silicon MOSFET

ATP108 — General-Purpose Switching Device Applications

Features

- · Low ON-resistance
- · Slim package
- · Halogen free compliance

- · Large current
- 4.5V drive
- · Protection diode in

Specifications

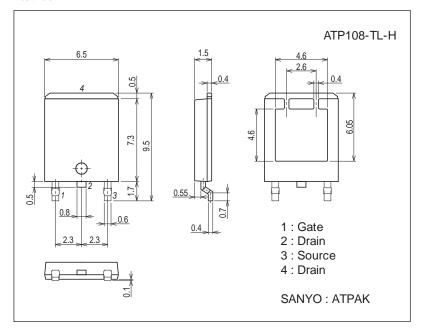
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		-40	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	ID		-70	Α
Drain Current (PW≤10μs)	I _{DP}	PW≤10μs, duty cycle≤1%	-210	Α
Allowable Power Dissipation	PD	Tc=25°C	60	W
Channel Temperature	Tch		150	C
Storage Temperature	Tstg		-55 to +150	C
Avalanche Energy (Single Pulse) *1	EAS		95	mJ
Avalanche Current *2	I _{AV}		-35	Α

Note :*1 V_{DD}=-15V, L=100μH, I_{AV}=-35A

Package Dimensions

unit : mm (typ) 7057-001



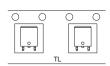
Product & Package Information

• Package : ATPAK

• JEITA, JEDEC :-

• Minimum Packing Quantity : 3,000 pcs./reel

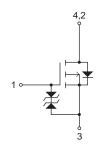
Packing Type: TL



Marking



Electrical Connection



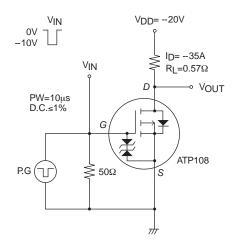
^{*2} L≤100µH, Single pulse

ATP108

Electrical Characteristics at Ta=25°C

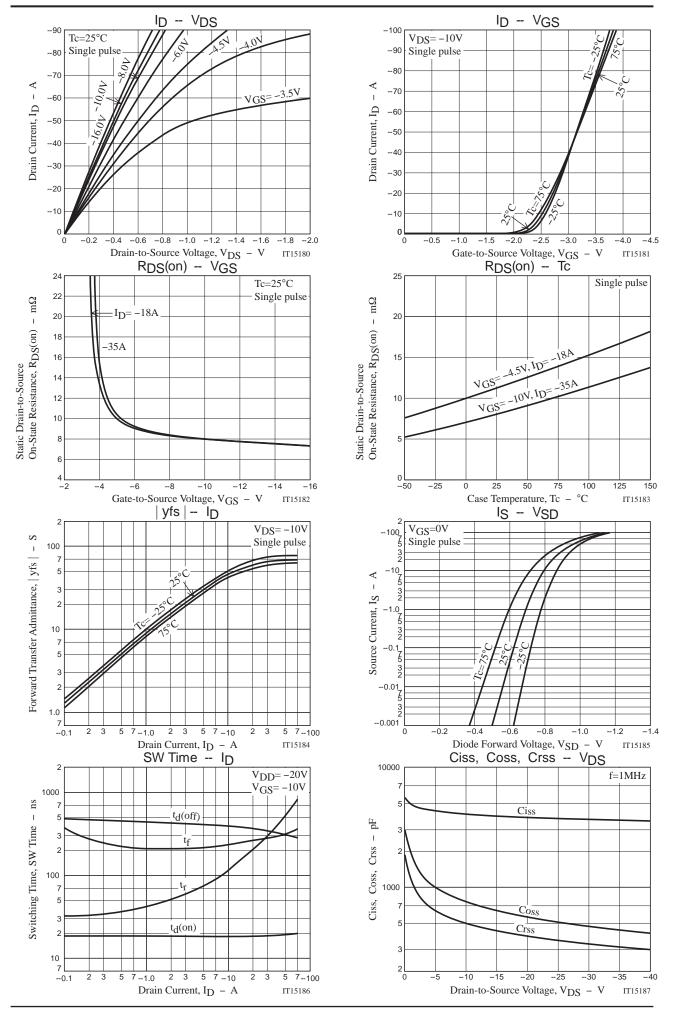
Parameter	Symbol	Conditions	Ratings			Unit	
Farameter	Symbol	Conditions	min	typ	max	Onit	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0V	-40			V	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =-40V, V _{GS} =0V			-1	μΑ	
Gate-to-Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0V			±10	μΑ	
Cutoff Voltage	VGS(off)	V _{DS} =-10V, I _D =-1mA	-1.5		-2.6	V	
Forward Transfer Admittance	yfs	V _{DS} =-10V, I _D =-35A		65		S	
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	I _D =-35A, V _G S=-10V		8	10.4	mΩ	
Static Drain-to-Source On-State Resistance	R _{DS} (on)2	I _D =-18A, V _G S=-4.5V		11.5	16.5	mΩ	
Input Capacitance	Ciss			3850		pF	
Output Capacitance	Coss	V _{DS} =-20V, f=1MHz		560		pF	
Reverse Transfer Capacitance	Crss			390		pF	
Turn-ON Delay Time	t _d (on)			19		ns	
Rise Time	t _r	See an edified Test Circuit		340		ns	
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		340		ns	
Fall Time	tf			290		ns	
Total Gate Charge	Qg			79.5		nC	
Gate-to-Source Charge Qgs	Qgs	V _{DS} =-20V, V _{GS} =-10V, I _D =-70A		20		nC	
Gate-to-Drain "Miller" Charge	Qgd			15		nC	
Diode Forward Voltage	VSD	IS=-70A, VGS=0V		-1.05	-1.5	V	

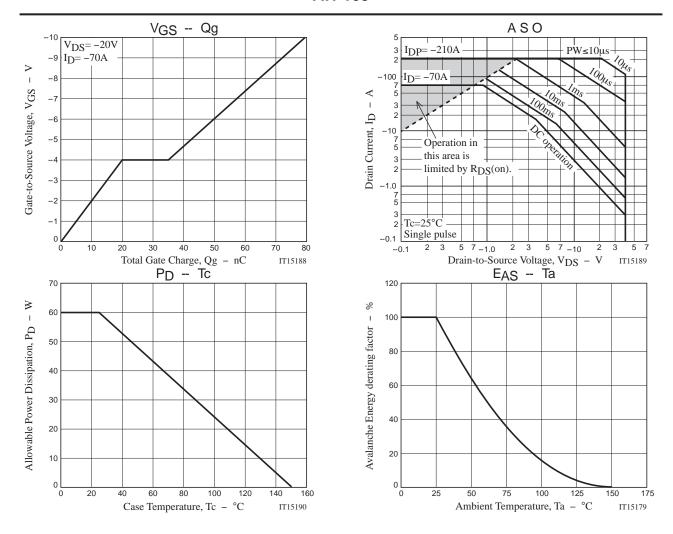
Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo		
ATP108-TL-H ATPAK		3,000pcs./reel	Pb Free and Halogen Free		



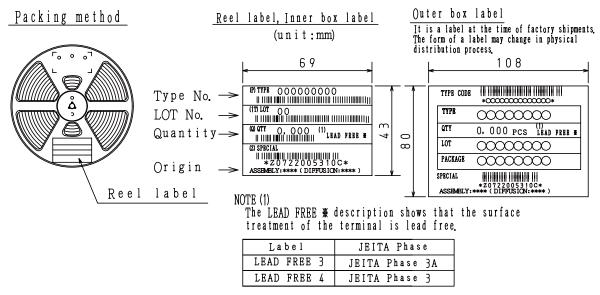


Taping Specification

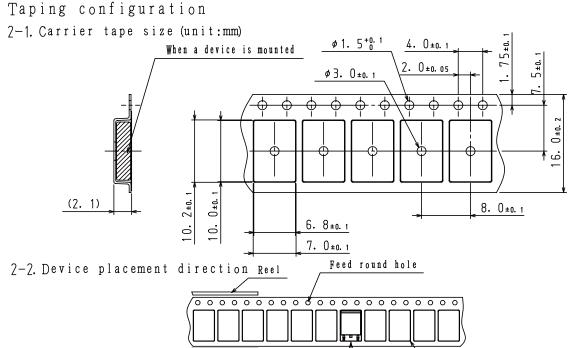
ATP108-TL-H

1. Packing Format (TL)

Package Name	Carrier Tape	Maximum Number of devices contained (pcs)			Packing format		
rackage Name	Туре	Reel	Inner box	Outer box	INNER BOX SD-C-18	OUTER BOX SD-A-18	
					1 reels contained	5 inner boxes contained	
ATPAK	ATP 3,000	3,000	3, 000 1	15,000	Dimensions:mm (external)	Dimensions:mm (external)	
					340×340×28	355×355×165	



7. Taping configuration



The one erectrode terminals on feed hole side····TL

ΤL

→ Feed direction

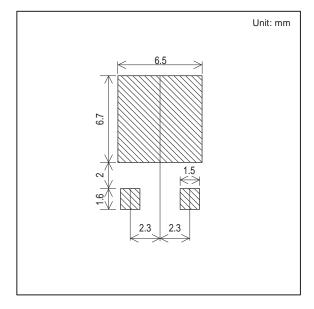
Carrier tape

Outline Drawing

ATP108-TL-H

Mass (g) Unit 0.266 For reference mm

Land Pattern Example



Note on usage: Since the ATP108 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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